

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

Ziko, Mehadi Hasan; Koel, Ants; Rang, Toomas; Toompuu, Jana Silicon Carbide and Related Materials 2019 : Selected peer-reviewed papers from International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), September 29 - October 4, 2019, Kyoto, Japan Materials science forum 2020 / p. 960-972 <https://doi.org/10.4028/www.scientific.net/MSF.1004.960>
[Conference proceedings at Scopus](#) [Article at Scopus](#)

Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures

Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas Materials characterization VII 2015 / p. 283-294 : ill

Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

Lebedev, Alexander A.; Davydovskaya, Klavdya S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptšuk, Natalja; Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 730-733 <https://doi.org/10.4028/www.scientific.net/MSF.963.730> [Conference proceeding at Scopus](#) [Article at Scopus](#)